



DMT10H009LPS

100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C		
100V	$8m\Omega$ @ $V_{GS} = 10V$	90A		
1007	12.5mΩ @ V _{GS} = 4.5V	74A		

Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{\text{DS(ON)}}$, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

Applications

- Motor Control
- DC-DC Converters
- Power Management

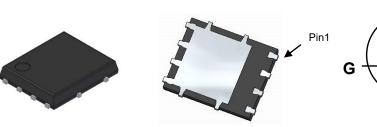
Features

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- · Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®] 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

PowerDI5060-8



Bottom View



Internal Schematic

Top View Pin Configuration

Ordering Information (Note 4)

Top View

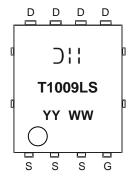
Part Number	Case	Packaging
DMT10H009LPS-13	PowerDI5060-8	2,500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information



] | | = Manufacturer's Marking T1009LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	100	V		
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current V _{GS} = 10V (Note 6)	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	10 8	А
Continuous Drain Current V _{GS} = 10V (Note 7)	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I _D	90 72	А
Pulsed Drain Current (10µs Pulse, T _C =+25°C, Package Lim	I _{DM}	360	Α		
Maximum Continuous Body Diode Forward Current			I _S	85	Α
Pulsed Body Diode Current (10µs Pulse, T _C =+25°C, Package Limited)			I _{SM}	360	Α
Avalanche Current (Note 8), L=0.3mH			I _{AS}	21	Α
Avalanche Energy (Note 8), L=0.3mH			E _{AS}	66	mJ
V _{DS} Spike, L=0.1mH t=10μs			V _{SPIKE}	110	V

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{ heta JA}$	98	°C/W
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	43	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P_{D}	104	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.2	°C/W
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +150	°C

Notes:

- $5. \ \, \text{Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. }$
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.



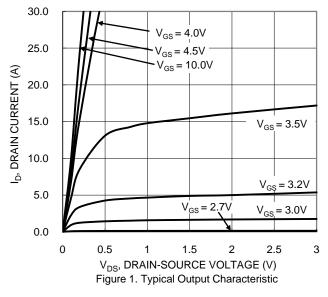
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1.2	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	6	8	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	9	12.5	11177	$V_{GS} = 4.5V, I_D = 5A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 13A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	2309			$V_{DS} = 50V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		536	_	pF		
Reverse Transfer Capacitance	Crss	_	13.7	_			
Gate Resistance	Rg	_	1.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	40.2	_			
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	20.2	_	nC	V 50V I 20A	
Gate-Source Charge	Q _{gs}	_	7.0	_	liC	$V_{DD} = 50V, I_D = 20A,$	
Gate-Drain Charge	Q_{gd}	_	8.5	_			
Turn-On Delay Time	t _{D(ON)}	_	5.4	_		V _{DD} = 50V, V _{GS} = 10V,	
Turn-On Rise Time	t _R	_	10.6	_			
Turn-Off Delay Time	t _{D(OFF)}	_	28.3	_	ns	$I_D = 20A, R_g = 3\Omega$	
Turn-Off Fall Time	t _F	_	14.9	_		-	
Reverse Recovery Time	t _{RR}	_	44.3	_	ns	1 004 37/31 4004/	
Reverse Recovery Charge	Q _{RR}	_	65.5	_	nC	I _F = 20A, di/dt = 100A/μs	

Notes:

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





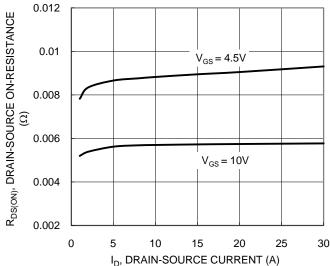


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

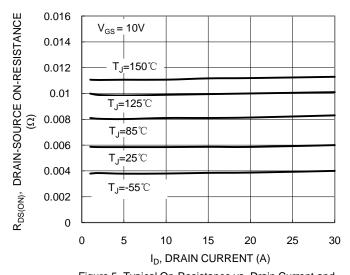
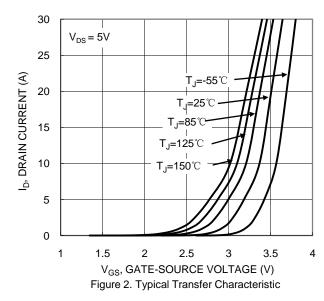


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



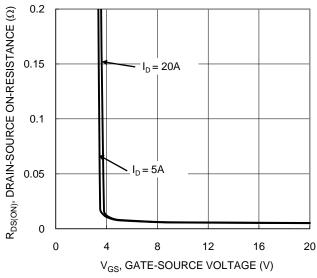


Figure 4. Typical Transfer Characteristic

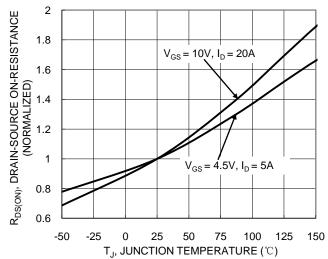


Figure 6. On-Resistance Variation with Junction Temperature





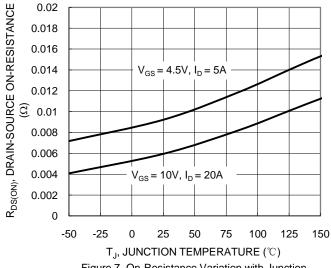
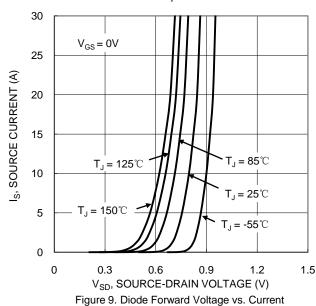


Figure 7. On-Resistance Variation with Junction Temperature



10 8 $V_{GS}(V)$ $V_{DS} = 50V, I_{D} = 20A$ 4 2 0 0 5 20 25 30 35 40 45 10 15 Qg (nC)

Figure 11. Gate Charge

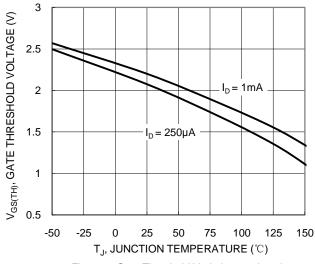
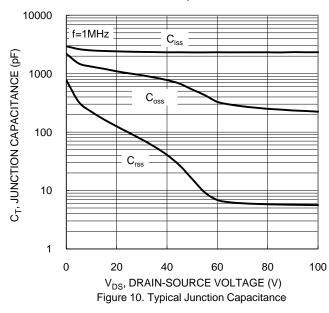
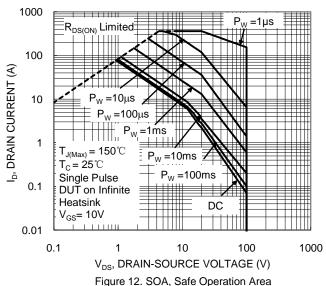


Figure 8. Gate Threshold Variation vs. Junction Temperature







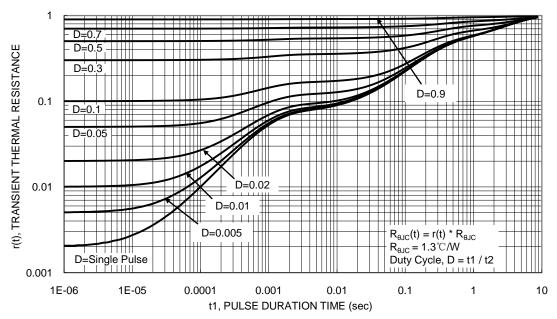


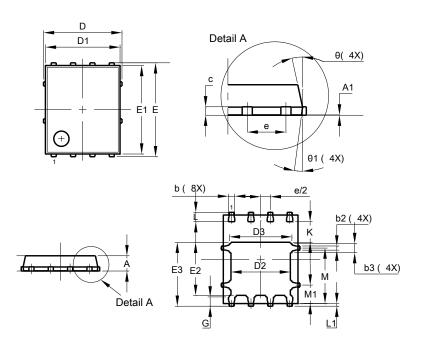
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

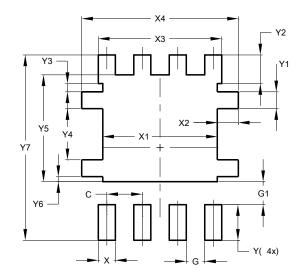


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC	,		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12º	11º		
Θ1	6°	8°	7º		
All	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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